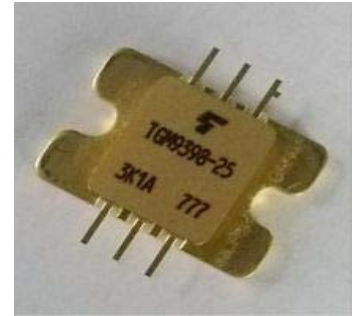


FEATURES

- BROAD BAND 2-STAGE AMPLIFIER
- HIGH POWER
P1dB= 44.0dBm at Pin= 23.0dBm
- HIGH GAIN
GL= 24dB(Typ) at Pin= 7dBm
- HERMETICALLY SEALED PACKAGE



RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power	Pout	VDD1,VDD2= 24V IDDset= 1.2A @Pin= 23.0dBm f = 9.3 to 9.8GHz	dBm	43.0	44.0	—
Drain Current	IDD*		A	—	2.6	3.5
Power Added Efficiency	η_{add}		%	—	38	—
Linear Gain	GL	@Pin= 7dBm	dB	20	24	—

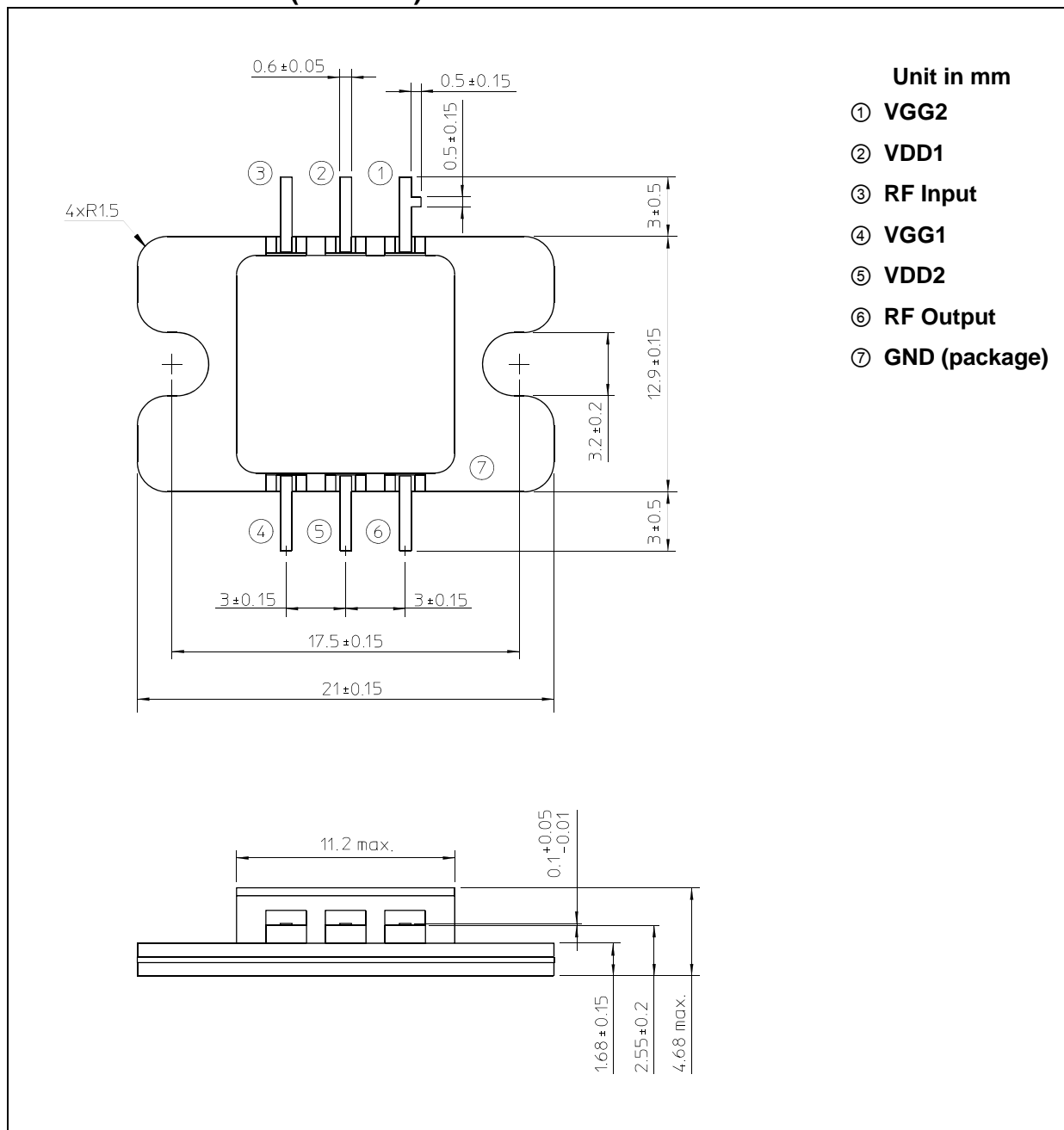
*IDD=IDD1+ IDD2

ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain- Source Voltage	VDD1, VDD2	V	50
Gate- Source Voltage	VGG1,VGG2	V	-10
Drain Current	IDD1	A	1.25
	IDD2	A	7.5
Flange Temperature	Tf	°C	-40 to +90
Input Power	Pin	dBm	+27
Storage Temperature	Tstg	°C	-65 to +175

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PACKAGE OUTLINE (7-BA42B)

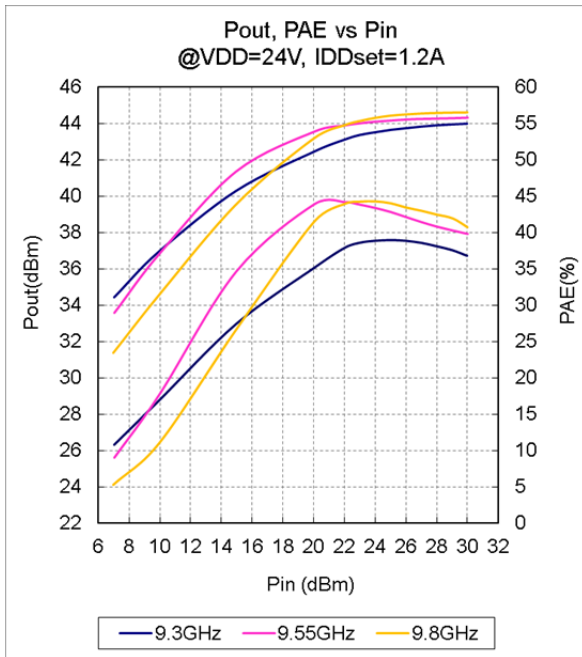


HANDLING PRECAUTIONS FOR PACKAGE MODEL

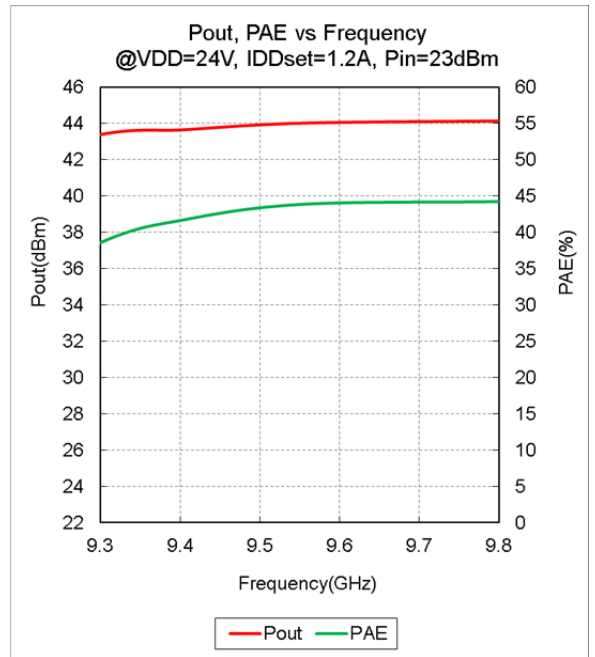
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds 350°C. Flanges of devices should be attached using screws and washers. Recommended torque is 0.18-0.20 N·m.

TYPICAL RF PERFORMANCE

· Pout, PAE vs. Pin



· Pout, PAE vs. Frequency



MEASUREMENT CIRCUIT SCHEMATIC

